

6. The method according to any one of the preceding claims, wherein the step of depositing the partially planarized organosilicate layer over the oxide comprises the step of spin-coating the partially planarized organosilicate layer onto the oxide.

5 7. The method according to claim 1, wherein the step of depositing the partially planarized organosilicate layer over the oxide comprises the step of spin-coating the partially planarized organosilicate layer onto the oxide, and

wherein the step of spin-coating the partially planarized organosilicate layer onto the oxide comprises even spin-on-glass.

8. The method according to claim 5, wherein the step of performing the dry plasma etch comprises the steps of doing a tuned etch to open the partially planarized organosilicate layer above the silicon nitride, and doing a short selective etch to remove only the HDP oxide layer, wherein the semiconductor wafer is etched in an oxide etcher.

5 9. The method according to any one of the preceding claims, wherein the step of non-selective etching uses gases selected from the group consisting of CF_4 , O_2 , and Ar.

10. The method according to any one of the preceding claims, wherein the step of selectively etching partial to oxide uses gases selected from the group consisting of C_5F_8 , O_2 , N_2 , and Ar.

10 11. The method according to one of the preceding claims, wherein after performing the dry plasma etch and before performing the CMP, remaining partially planarized organosilicate is stripped off.

12. The method according to claim 11, comprising the step of performing an oxidizing ash to strip off the remaining partially planarized organosilicate.

15 13. The method according to claim 11, comprising the step of performing an HF strip to strip off the remaining partially planarized organosilicate.